Triacs BT139X series

GENERAL DESCRIPTION

Glass passivated triacs in a full pack, plastic envelope, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

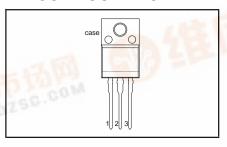
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
- 括岡	BT139X- BT139X- BT139X-	500 500F 500G	600 600F 600G	800 800F 800G	
V_{DRM}	Repetitive peak off-state	500	600	800	V
I _{T(RMS)} I _{TSM}	voltages RMS on-state current Non-repetitive peak on-state current	16 140	16 140	16 140	A A

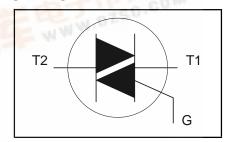
PINNING - SOT186A

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	THE.	MAX.	50	UNIT
V_{DRM}	Repetitive peak off-state voltages	- AM 67 2E	13	-500 500 ¹	-600 600 ¹	-800 800	V
I _{T(RMS)} I _{TSM}	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{hs} \le 38$ °C full sine wave; $T_j = 25$ °C prior to surge	-		16		А
4000	M. M. A.	t = 20 ms	-		140		A
l²t dl _⊤ /dt	I ² t for fusing Repetitive rate of rise of on-state current after	t = 16.7 ms t = 10 ms $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $dI_G/dt = 0.2 \text{ A}/\mu\text{s}$	-		150 98		A A ² s
	triggering	T2+ G+ T2+ G- T2- G- T2- G+	Œ	WW	50 50 50 10		A/μs A/μs A/μs A/μs
I_{GM} V_{GM} P_{GM}	Peak gate current Peak gate voltage Peak gate power Average gate power	over any 20 ms period	- - -		2 5 5 0.5		Ä V W
P _{G(AV)} T _{stg} T _j	Storage temperature Operating junction temperature	gvor arry 20 mo period	-40 -		150 125		Ç

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 $T_{hs} = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	R.M.S. isolation voltage from all three terminals to external heatsink	f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	ı		2500	>
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	ı	10	1	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-hs}	Thermal resistance junction to heatsink	full or half cycle with heatsink compound without heatsink compound	1 1		4.0 5.5	K/W K/W
R _{th j-a}	Thermal resistance junction to ambient	in free air	-	55	-	K/W

STATIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.		MAX.		UNIT
I _{GT}	Gate trigger current	BT139X- $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$:	.:F	G	
G1	33	T2+ G+ T2+ G-	-	5 8	35 35	25 25	50 50	mA mA
		T2- G- T2- G+	-	10 22	35 70	25 70	50 100	mA mA
IL	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$ T2+ G+	_	7	40	40	60	mA
		T2+ G- T2- G-	-	20 8	60 40	60 40	90 60	mA mA
I _H	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	- -	10 6	60 30	60 30	90 60	mA mA
V_{T}	On-state voltage Gate trigger voltage	$I_T = 20 \text{ A}$ $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$ $V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$	- - 0.25	1.2 0.7 0.4		1.6 1.5 -		V V V
I _D	Off-state leakage current	$T_{j} = 125 ^{\circ}\text{C}$ $V_{D} = V_{DRM(max)};$ $T_{j} = 125 ^{\circ}\text{C}$	-	0.1		0.5		mA

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DYNAMIC CHARACTERISTICS

T_i = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		TYP.	MAX.	UNIT
dV _D /dt	Critical rate of rise of off-state voltage	BT139X- $V_{DM} = 67\% V_{DRM(max)};$ $T_i = 125 °C;$ exponential	 100	F 50	G 200	250	-	V/μs
dV _{com} /dt	Critical rate of change of commutating voltage	waveform; gate open circuit $V_{DM} = 400 \text{ V}; T_j = 95 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dI_{com}/dt = 7.2 \text{ A/ms}; gate$	-		10	20	-	V/µs
t _{gt}	Gate controlled turn-on time	open circuit $I_{TM} = 20 \text{ A}; V_D = V_{DRM(max)}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu s$	-	-	-	2	-	μs

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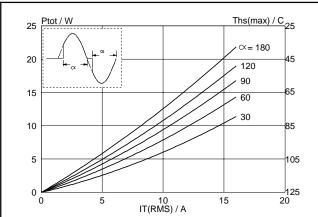


Fig.1. Maximum on-state dissipation, P_{tot} , versus rms on-state current, $I_{T(RMS)}$, where α = conduction angle.

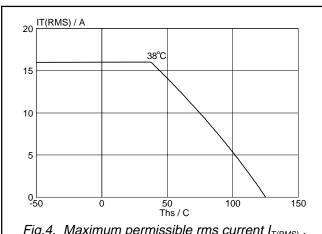


Fig.4. Maximum permissible rms current $I_{T(RMS)}$, versus heatsink temperature T_{hs} .

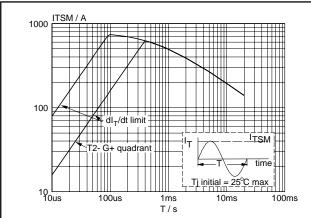


Fig.2. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus pulse width t_p , for sinusoidal currents, $t_p \le 20$ ms.

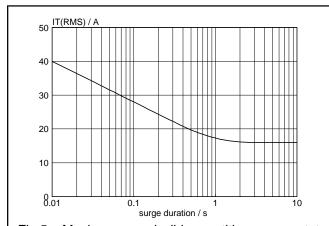


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(RMS)}$, versus surge duration, for sinusoidal currents, f = 50 Hz; $T_{hs} \le 38$ °C.

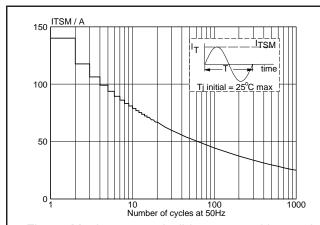


Fig.3. Maximum permissible non-repetitive peak on-state current I_{TSM} , versus number of cycles, for sinusoidal currents, f = 50 Hz.

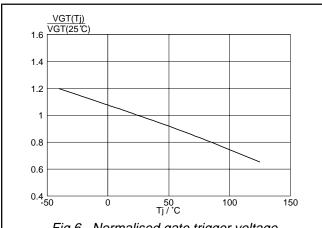
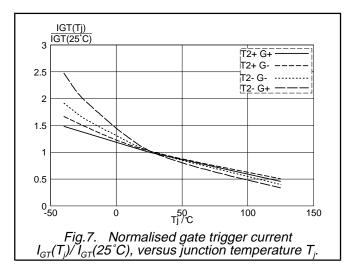
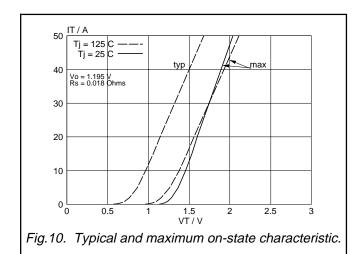


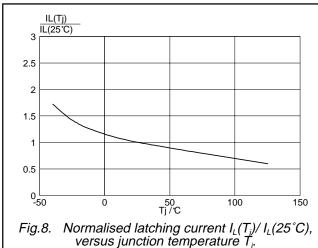
Fig.6. Normalised gate trigger voltage $V_{GT}(T_j)/V_{GT}(25^{\circ}C)$, versus junction temperature $T_{j\cdot}$

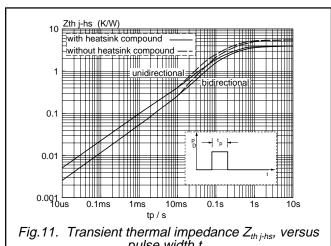
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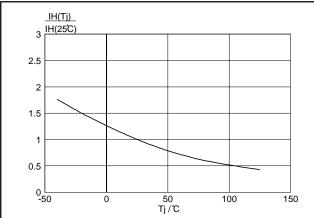
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pulse width t_n.

Fig.9. Normalised holding current $I_H(T_i)/I_H(25^{\circ}C)$, versus junction temperature T_i .

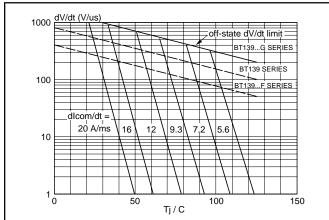
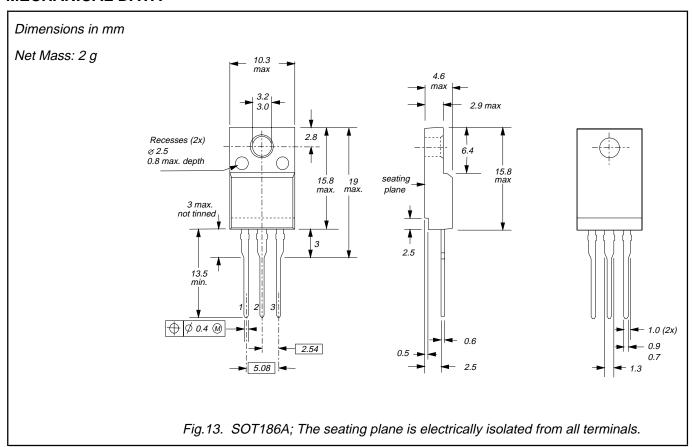


Fig.12. Typical commutation dV/dt versus junction temperature, parameter commutation dl_T/dt. The triac should commutate when the dV/dt is below the value on the appropriate curve for pre-commutation dl_r/dt.

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MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for F-pack envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status						
Objective specification	This data sheet contains target or goal specifications for product development.					
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.					
Product specification	This data sheet contains final product specifications.					
1 reduct openineation	The data check contains into product opening and in					

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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